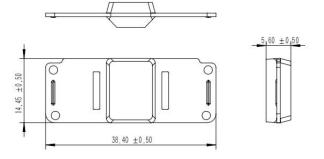


XT4550M-B接线盒模块 Integrated Diode





FEATURES

- Low forward voltage drop
- Low leakage current
- Super-long operating life
- High forward surge capability
- Easy installation
- Terminals: Copper (tin-plated)
- ESD ≥20kW
- Plastic packaging: UL
 94 Flammability Classification V-0

	SYMBOL	VALUE	UNITS
Minimun Reverse Voltage, Repetitive	VRRM	45	v
Tj 25°C Ir<0.5mA			
Maximum DC Blocking Voltage	V _{DC}	45	V
Tj 25℃ lr<0.5mA			
Maximum Average Forward Current Tj 150℃	I _{FAV}	45	Α
Peak Forward Surge Current	FSM (surge)	400	A
8.3ms single half-wave superimposed on rated load (JEDEC method)			
Maximum Instantaneous Forward Voltage	V _F , T _j = 25°C	0.50	V
	V _F , T _j = 150°C	0.30	V
Maximum Reverse Current at DC Blocking Voltage	I _R , TA = 25℃	0.1	mA
	I _R , TA = 100℃	50	mA
Operating Junction Temperature in DC Forward Mode	T _j , t ≤ 1h	200	°C
Thermal Resistance to Case	R _{θjc}	0.8	°C/W
Storage Temperature Range	T _{STG}	-55 ~ +150	°C



XT4550M-B印字要求:

